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Schematic diagram

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NCE4060K

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Marking and pin assignment

TO-252-2L top view

NCE

(1) GO

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE4060K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} =40V,I_D =60A
 R_{DS(ON)} <13mΩ @ V_{GS}=10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAs
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4060K	NCE4060K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	60	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	42	А
Pulsed Drain Current	I _{DM}	200	А
Maximum Power Dissipation	PD	65	W
Derating factor		0.43	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	400	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C





NCE4060K

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{ejc}	2.3	°C/W
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Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40	45	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.2	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	7.3	13	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =20A	15	-	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C _{lss}		-	1800	-	PF
Output Capacitance	C _{oss}	V _{DS} =20V,V _{GS} =0V, F=1.0MHz	-	280	-	PF
Reverse Transfer Capacitance	C _{rss}		-	190	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t _{d(on)}		-	6.4	-	nS
Turn-on Rise Time	tr	V_{DD} =20V, I_D =2A, R_L =1 Ω	-	17.2	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	29.6	-	nS
Turn-Off Fall Time	t _f		-	16.8	-	nS
Total Gate Charge	Qg)/ _20)// _20 A	-	29		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=20V, I_{D}=20A,$	-	4.5		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	6.4		nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =10A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	60	А
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	29	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	26	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LE				y LS+LD)

Notes:

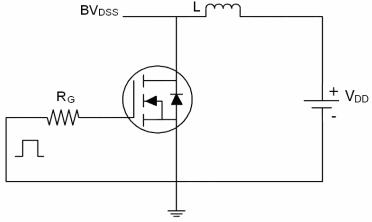
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, t \leq 10 sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. E_{AS} condition : Tj=25 $^\circ\!\!\mathrm{C}$,V_{DD}=20V,V_G=10V,L=1mH,Rg=25\Omega,



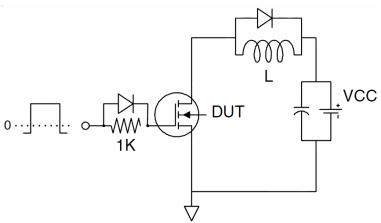
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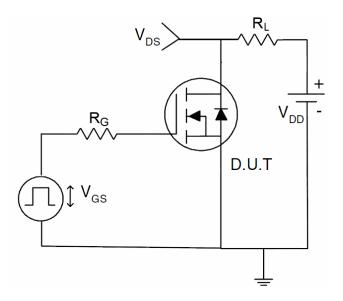
Test circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



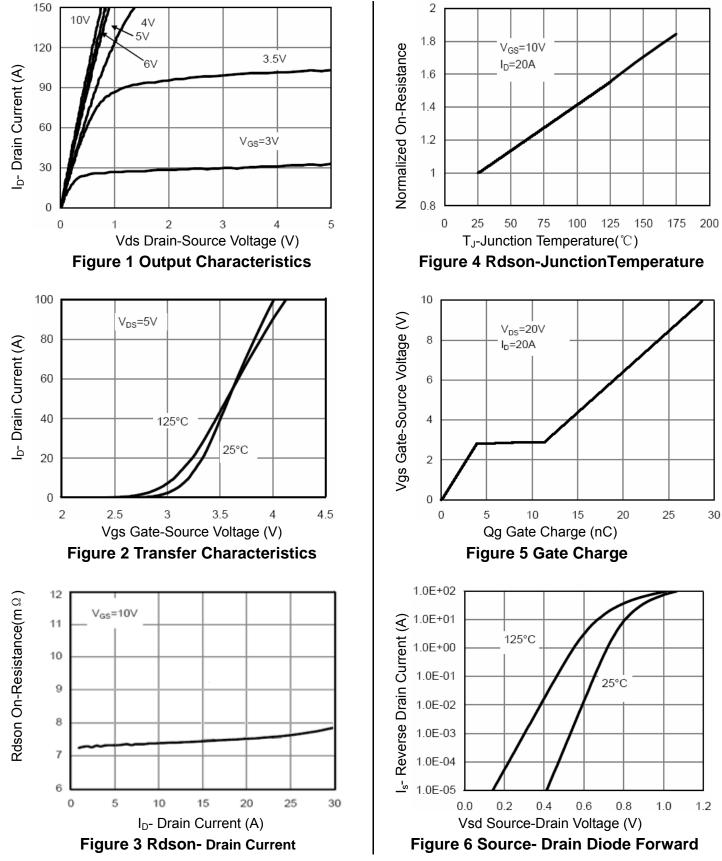
3) Switch Time Test Circuit







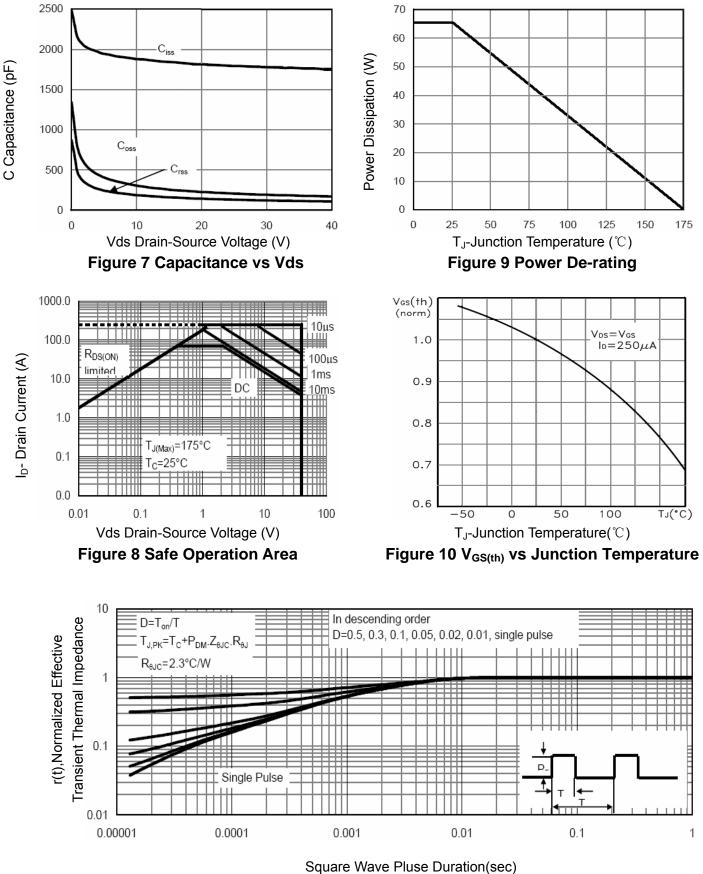
Typical Electrical and Thermal Characteristics (Curves)

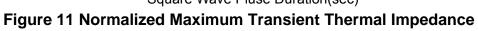




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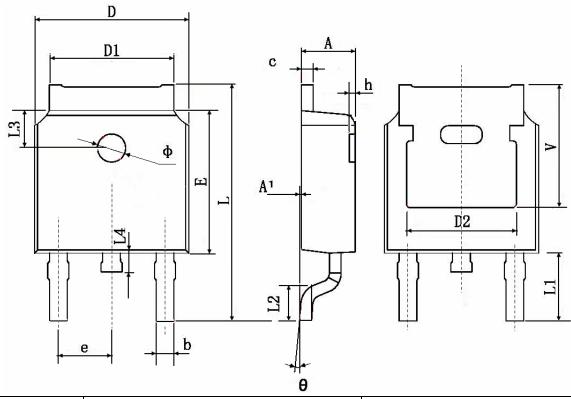




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TO-252 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	4.830 TYP. 0.190 TYP.			
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	900 TYP. 0.1		4 TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600	TYP.	0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		





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